

• General Description

The ZM420P06D combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

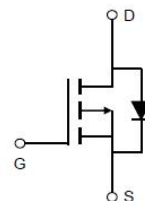
• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

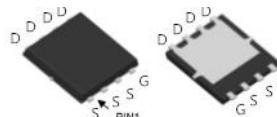
• Product Summary



$$V_{DS} = -60V$$

$$R_{DS(ON)} = 42m\Omega$$

$$I_D = -16A$$



DFN3*3

• Ordering Information:

Part NO.	ZM420P06M
Marking	ZM420P06
Packing Information	REEL TAPE
Basic ordering unit (pcs)	5000

• Absolute Maximum Ratings ($T_c = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 25	V
Continuous Drain Current	$I_{D@TC=25^\circ C}$	-16	A
	$I_{D@TC=75^\circ C}$	-12	A
	$I_{D@TC=100^\circ C}$	-10	A
Pulsed Drain Current ^①	I_{DM}	-48	A
Total Power Dissipation ^②	$P_{D@TC=25^\circ C}$	50	W
Total Power Dissipation	$P_{D@TA=25^\circ C}$	1.25	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	E_{AS}	45	mJ

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case ^②	R_{thJC}	-	-	2.4	°C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	65	°C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-60			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.2		-2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=-60V, V_{GS}=0V$			-1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-5A$		42	50	m Ω
		$V_{GS}=-4.5V, I_D=-3A$		65	75	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=-10V, I_D=-5A$		9		s
Source-drain voltage	V_{SD}	$I_S=-5A$			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	f = 1MHz	-	1050	-	pF
Output capacitance	C_{oss}		-	255	-	
Reverse transfer capacitance	C_{rss}		-	185	-	

•Gate Charge characteristics($T_a = 25^\circ C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD}=25V$ $I_D=4A$ $V_{GS}=10V$	-	11	-	nC
Gate - Source charge	Q_{gs}		-	5	-	
Gate - Drain charge	Q_{gd}		-	7	-	

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;

Fig.1 Gate-Charge Characteristics

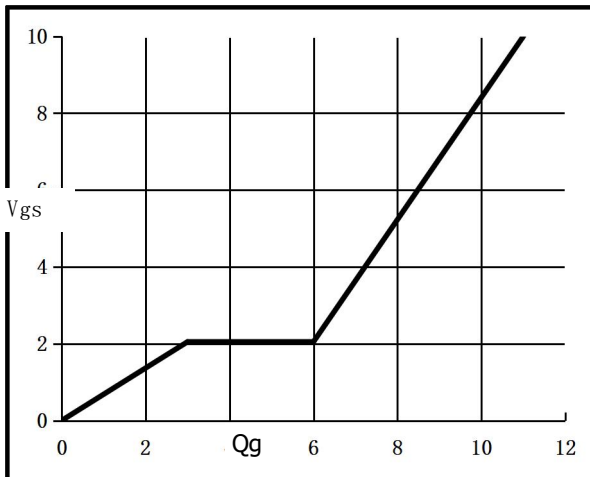


Fig.2 Capacitance Characteristics

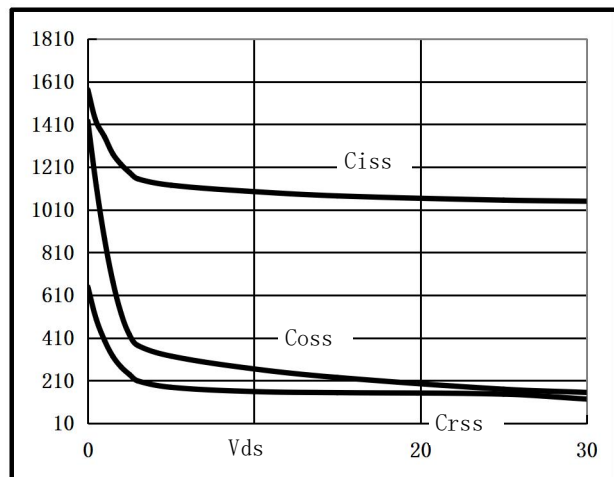


Fig.3 Power Dissipation Derating Curve

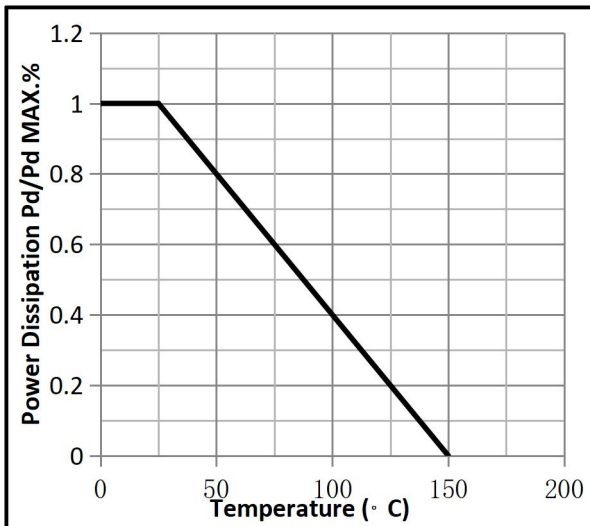


Fig.4 Typical output Characteristics

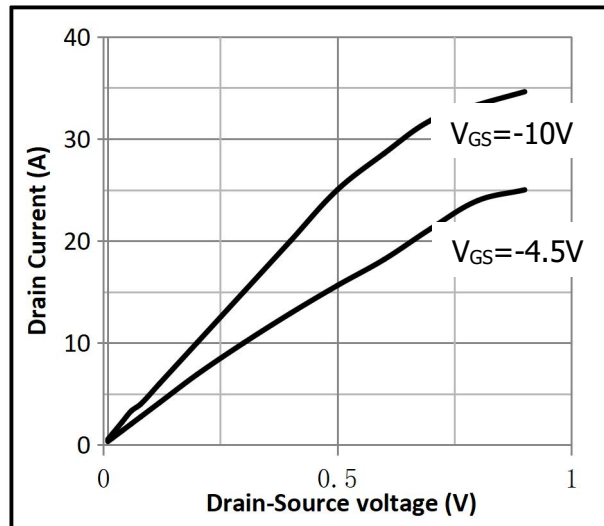


Fig.5 Threshold Voltage V.S Junction Temperature

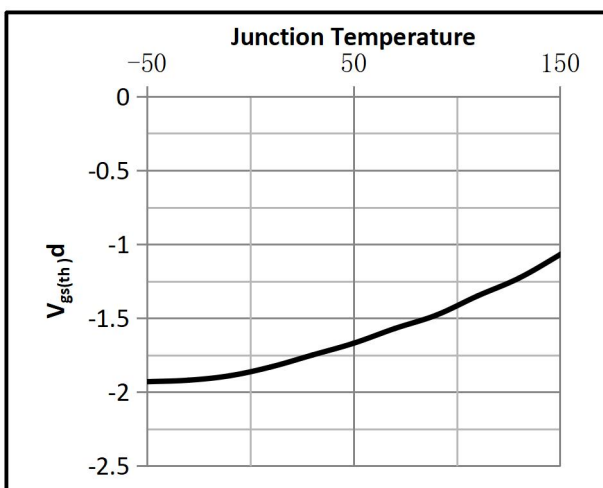


Fig.6 Resistance V.S Drain Current

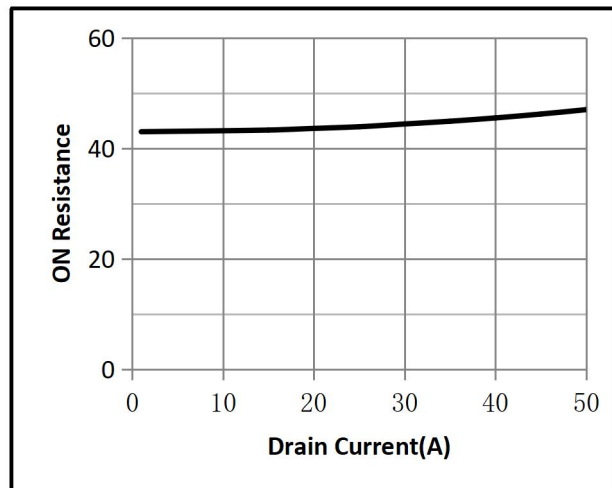


Fig.7 On-Resistance VS Gate Source Voltage

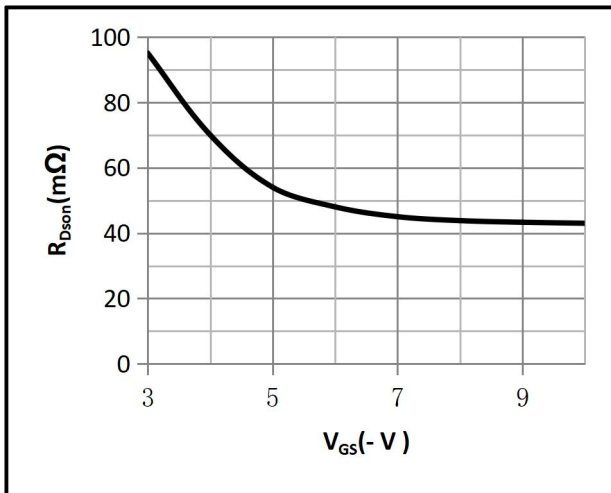


Fig.8 On-Resistance V.S Junction Temperature

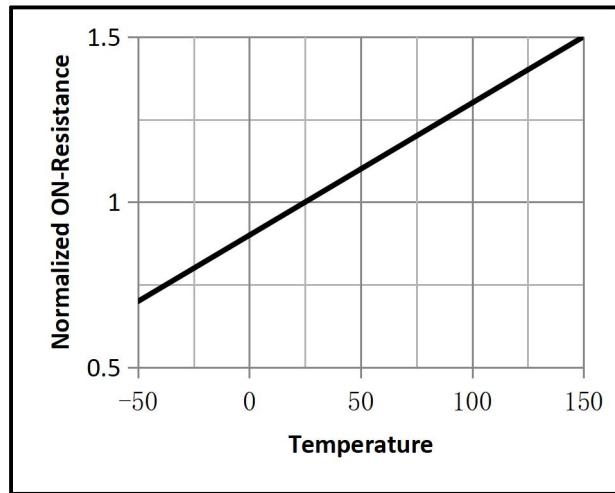


Fig.9 Switching Time Measurement Circuit

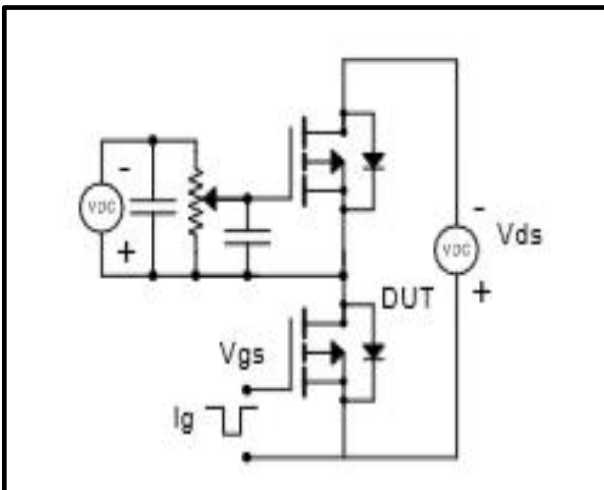


Fig.10 Gate Charge Waveform

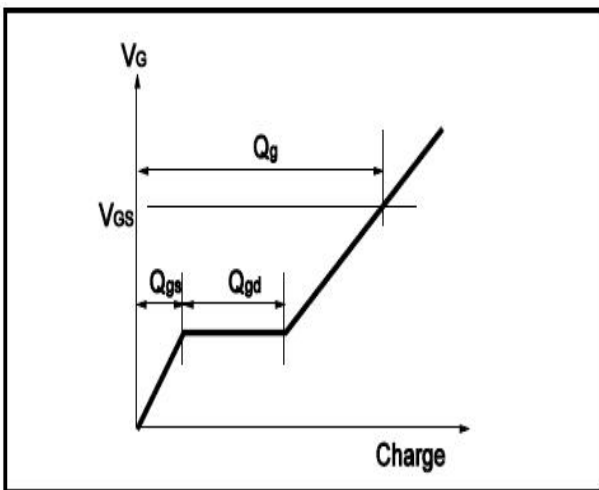


Fig.11 Switching Time Measurement Circuit

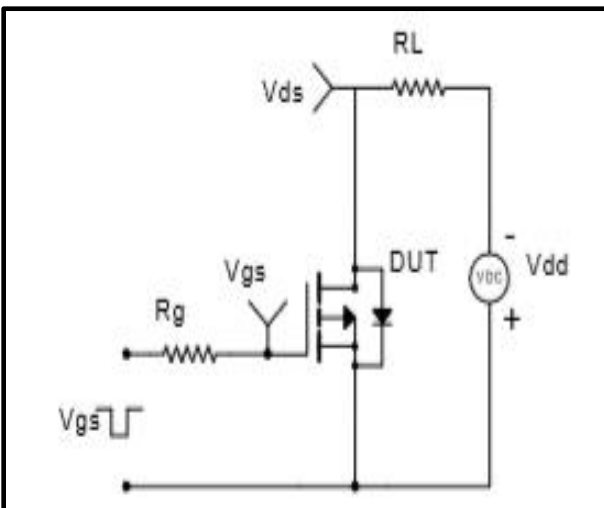
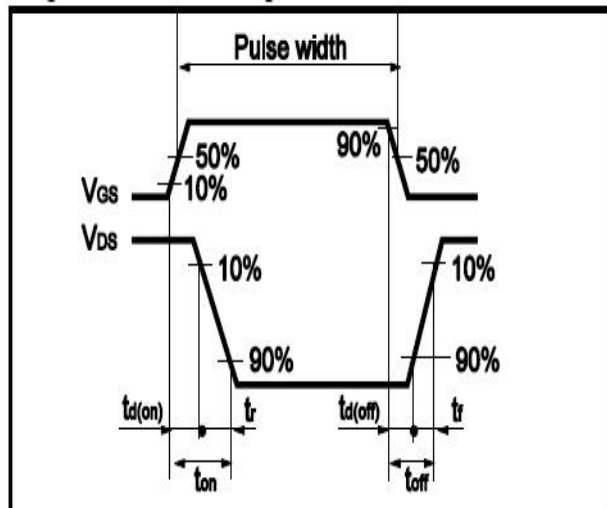
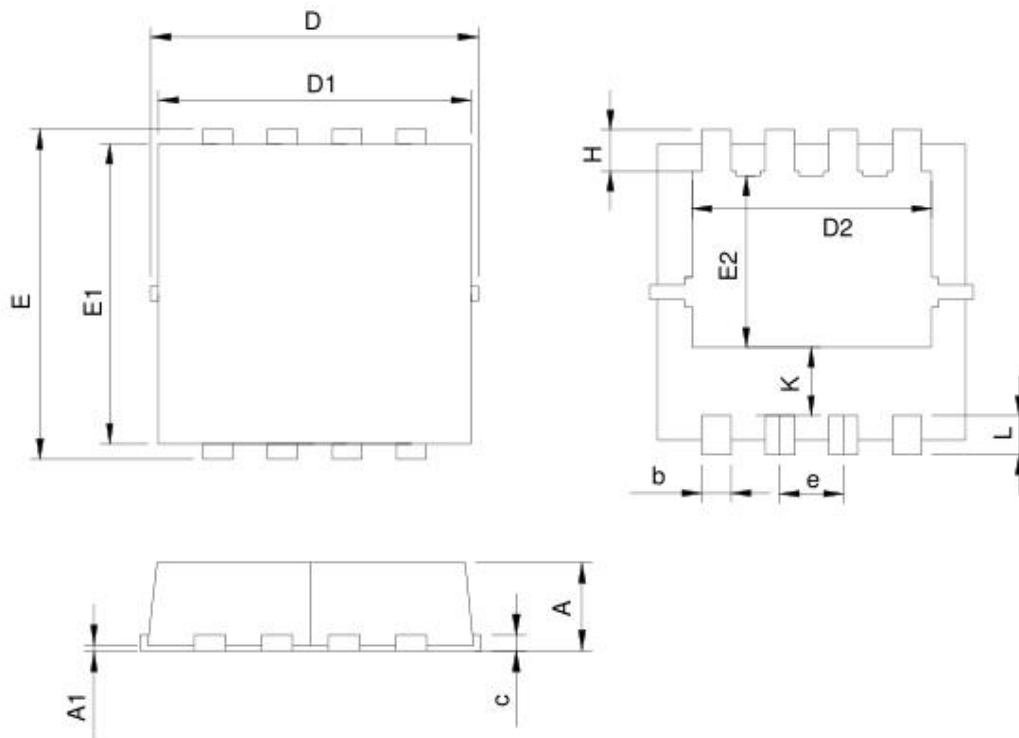


Fig.12 Gate Charge Waveform



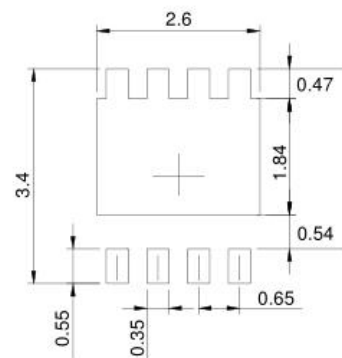
•Dimensions(DFN3×3)

Unit: mm



SYMBOL	DFN3.3x3.3-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039
A1	0.00	0.05	0.000	0.002
b	0.25	0.35	0.010	0.014
c	0.14	0.20	0.006	0.008
D	3.10	3.50	0.122	0.138
D1	3.05	3.25	0.120	0.128
D2	2.35	2.55	0.093	0.100
E	3.10	3.50	0.122	0.138
E1	2.90	3.10	0.114	0.122
E2	1.64	1.84	0.065	0.072
e	0.65 BSC		0.026 BSC	
H	0.32	0.52	0.013	0.020
K	0.59	0.79	0.023	0.031
L	0.25	0.55	0.010	0.022

RECOMMENDED LAND PATTERN



UNIT: mm

Note: ① Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$;

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;

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